



Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	90mΩ @ V _{GS} = -10V	-3.8A
-30V	134mΩ @ V _{GS} = -4.5V	-3.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General purpose interfacing switches
- Power management functions
- Load switch for portable devices

P-CHANNEL ENHANCEMENT MODE MOSFET

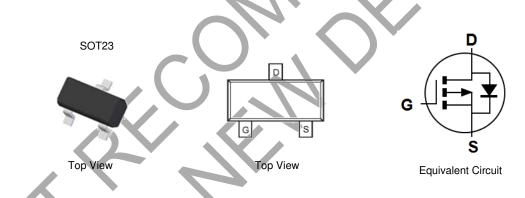
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMG2307LQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ©3
 - Weight: 0.08 grams (Approximate)



Ordering Information (Note 4)

Part Number	Baakaga	Packing		
Part Nulliber	Package	Qty.	Carrier	
DMG2307LQ-7	SOT23	3,000	Tape & Reel	

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

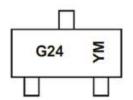
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



 $\begin{array}{l} G24 = Product \ Type \ Marking \ Code \\ YM = Date \ Code \ Marking \\ Y \ or \ \overline{Y} = Year \ (ex: \ J = 2022) \\ M = Month \ (ex: \ 9 = September) \end{array}$

Date Code Key

Year	2018		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	F		J	К	L	М	Ν	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Month	Jall	reb	Iviai	Арі	iviay	Juli	oui	Aug	Jeb	001	NOV	Dee

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	-30	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) $V_{GS} = -10V$	Steady State	TA = +25°C TA = +70°C	lo	-2.5 -2.0	А
Continuous Drain Current (Note 6) $V_{GS} = -10V$	Steady State	TA = +25°C TA = +70°C	lD	-3.8 -3.0	А
Continuous Drain Current (Note 6) $V_{GS} = -10V$	t ≤ 10sec	TA = +25°C TA = +70°C	lo	-4.6 -3.6	А
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	TA = +25°C TA = +70°C	lp	-3.1 -2.5	А
Pulsed Drain Current (Note 6)			Ідм	-20	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	0.76	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	159	°C/W
Total Power Dissipation (Note 6)	PD	1.36	W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	94	°C/W
Total Power Dissipation (Note 6) $t \le 10 \text{sec}$	PD	1.9	W
Thermal Resistance, Junction to Ambient (Note 6) t ≤ 10sec	R _{0JA}	65.8	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1 inch square copper plate.



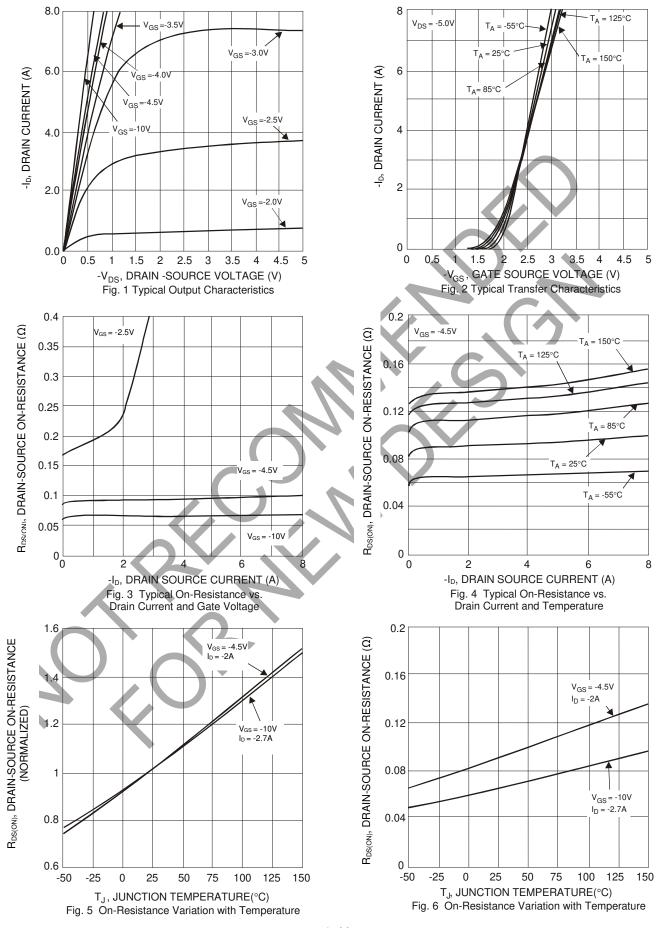
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			• 76		•	
Drain-Source Breakdown Voltage	BVDSS	-30	—	—	V	$V_{GS} = 0V, I_{D} = -250 \mu A$
Zero Gate Voltage Drain Current @T _C = +25°	C Idss	_	_	-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	VGS(TH)	-1.0		-3.0	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$
Static Drain-Source On-Resistance	Brayou		70	90	mΩ	$V_{GS} = -10V, I_D = -2.5A$
Static Dialit-Source On-Resistance	RDS(ON)		105	134	11152	VGS = -4.5V, ID = -2.5A
Forward Transfer Admittance	Y _{fs}	—	4.8	—	S	$V_{DS} = -10V, I_D = -2.5A$
Diode Forward Voltage	Vsd	—	-0.75	-1.0	N	$V_{GS} = 0V$, $I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	371.3		рF	
Output Capacitance	Coss	_	51.3	-	pF	V _{DS} = -15V, V _{GS} = 0V - f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	45.9		pF	
Gate Resistance	Rg	—	17	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	—	4.0	T	nC	
Total Gate Charge (V _{GS} = -10V)	Qg	—	8.2		nC	- VDS = -15V, ID = -3A
Gate-Source Charge		—	0.9	-	nC	VDS = -15V, $ID = -3A$
Gate-Drain Charge	Q _{gd}		1.2		nC	
Turn-On Delay Time	td(on)		4.8	_	ns	
Turn-On Rise Time	tR		7.3	—	ns	V _{DS} = -15V, V _{GS} = -10V R _L = 15Ω, R _G = 6Ω
Turn-Off Delay Time	td(off)	-	22.4		ns	$H_L = 15\Omega, H_G = 6\Omega$
Turn-Off Fall Time	tF		13.4		ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.



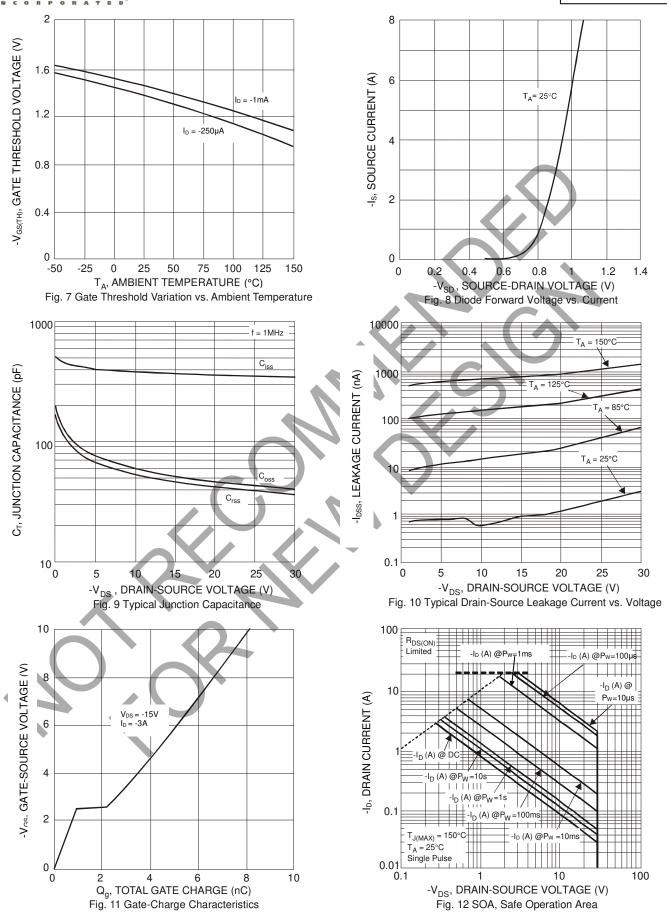
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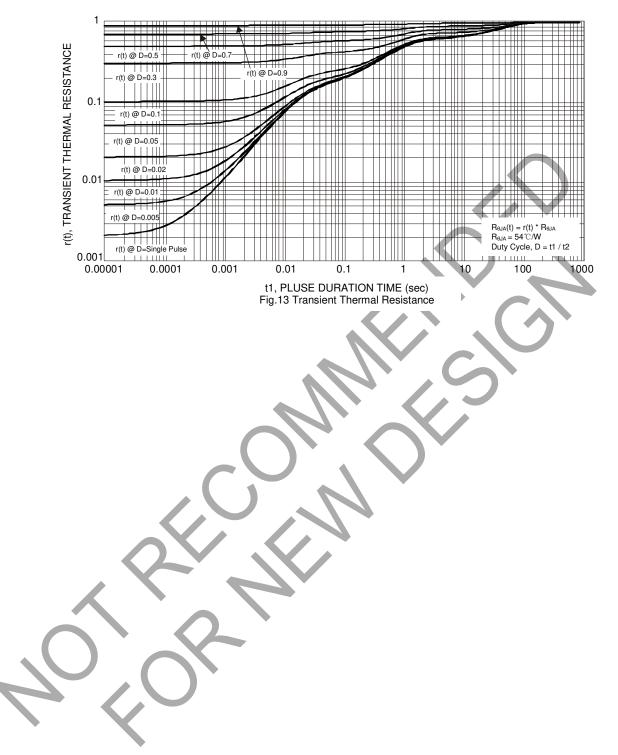
DMG2307LQ Document number: DS41313 Rev. 2 - 3 4 of 8 www.diodes.com







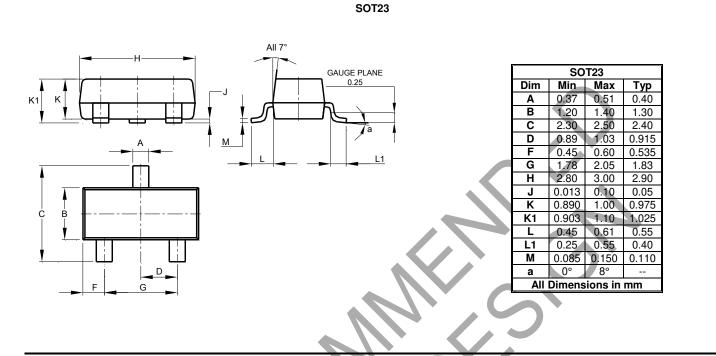






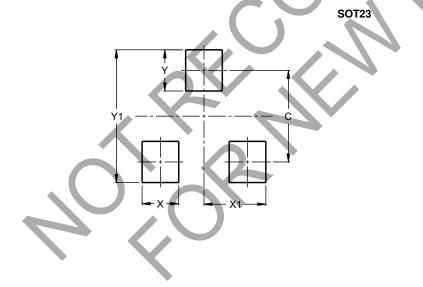
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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